SUD50P04-08



Vishay Siliconix

RoHS COMPLIANT

HALOGEN

FREE

P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (TYP.)	
-40	0.0081 at V_{GS} = -10 V	-50 ^d	60	
-40	0.0117 at V_{GS} = -4.5 V	-48 ^d	00	

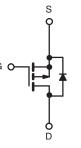


FEATURES

- TrenchFET[®] power MOSFET
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Power switch
- Load switch in high current applications
- DC/DC converters



P-Channel MOSFET

Ordering Information:

SUD50P04-08-GE3 (lead (Pb)-free and halogen-free)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \degree C$, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	-40	V
Gate-Source Voltage		V _{GS}	± 20	V
	T _C = 25 °C		-50 ^d	Δ
Continuous Drain Current ($T_J = 150 \ ^{\circ}C$)	T _C = 70 °C	I _D	-50 ^d	
Pulsed Drain Current		I _{DM}	-100	A
Avalanche Current		I _{AS}	-46	
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	106	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	Р	73.5 ^b	W
Maximum Fower Dissipation "	T _A = 25 °C °	– P _D –	2.5	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)	R _{thJC}	1.7	C/W	

Notes

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

- c. When mounted on 1" square PCB (FR-4 material).
- d. Package limited.

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS}=0~V,~I_{D}=-250~\mu A$	-40	-	-	- V 2.5
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	-1	-	-2.5	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 250	nA
		V_{DS} = -40 V, V_{GS} = 0 V	-	-	-1	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = -40 V, V_{GS} = 0 V, T_{J} = 125 °C	-	-	-50	μA
		V_{DS} = -40 V, V_{GS} = 0 V, T_{J} = 150 °C	-	-	-250	
On-State Drain Current ^a	I _{D(on)}	V_{DS} \leq -10 V, V_{GS} = -10 V	-50	-	-	А
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -22 \text{ A}$	-	0.0067	0.0081	Ω
	"DS(on)	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -19 \text{ A}$	-	0.0097	0.0117	32
Forward Transconductance ^a	g fs	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -22 \text{ A}$	-	45	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = -20 V, f = 1 MHz	-	5380	-	
Output Capacitance	Coss		-	570	-	pF
Reverse Transfer Capacitance	C _{rss}		-	500	-	
Total Cata Charge 6	0	$V_{DS} = -20 V, V_{GS} = -10 V, I_D = -20 A$	-	106	159	nC
Total Gate Charge ^c	Qg		-	60	90	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = -20 V, V_{GS} = -4.5 V, I_{D} = -20 A	-	22	-	
Gate-Drain Charge ^c	Q _{gd}		-	27	-	
Gate Resistance	Rg	f = 1 MHz	0.4	1.8	3.6	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	15	23	
Rise Time ^c	t _r	$V_{DD} = -20 V, R_1 = 2 \Omega$	-	12	18	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong -10~\text{A},~V_{GEN}=-10~\text{V},~R_g=1~\Omega$	-	70	105	ns
Fall Time ^c	t _f		-	18	27	
Drain-Source Body Diode Ratings a		stics (T _C = 25 °C) ^b		1		
Continuous Current	I _S		-	-	-50	
Pulsed Current	I _{SM}		-	-	-100	A
Forward Voltage ^a	V _{SD}	I _F = -10 A, V _{GS} = 0 V	-	-0.8	-1.5	V
Reverse Recovery Time	trr		-	35	53	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = -10 A, dl/dt = 100 A/μs	-	-2	-3	А
Reverse Recovery Charge	Q _{rr}		-	33	50	nC

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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For technical questions, contact: <u>pmostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u> V_{GS} = 10 V thru 5 V $V_{GS} = 4 V$ 0.012

0.015



ISHAY www.vishay.com

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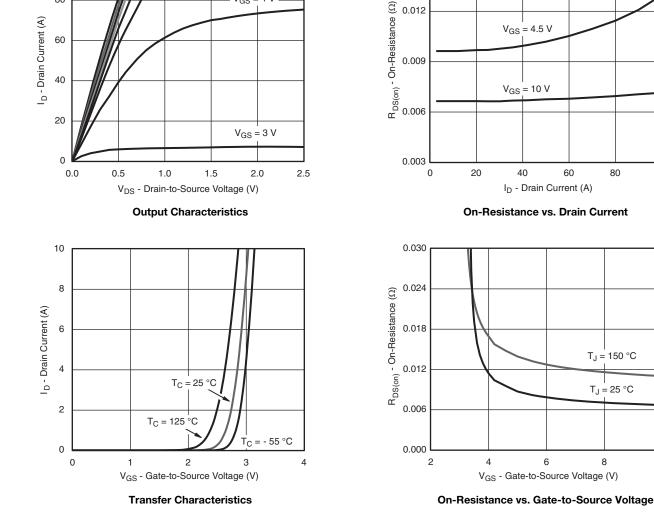
80

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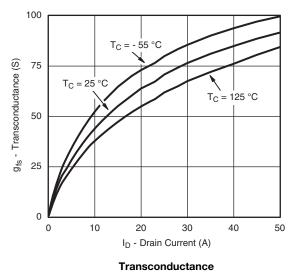
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SUD50P04-08



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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Document Number: 65594

120

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10

8

6

4

2

0

0

V_{GS} - Gate-to-Source Voltage (V)

I_D = 20 Å

30

 $V_{DS} = 20 V$

60

Q_g - Total Gate Charge (nC)

Gate Charge

= 10 V V_{DS}

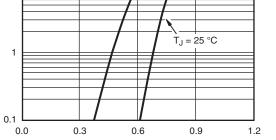
V_{DS} = 32 V

90

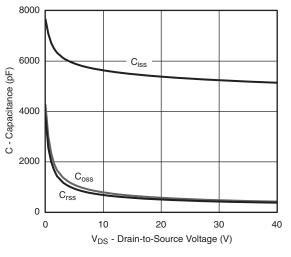
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S14-2535-Rev. B, 29-Dec-14

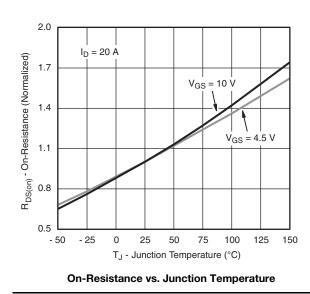
T_J = 25 °C



V_{SD} - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage







S14-2535-Rev. B, 29-Dec-14

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

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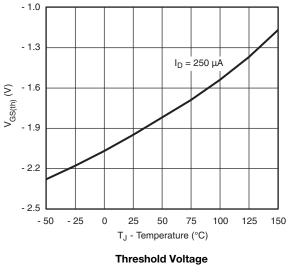
T_J = 150 °C

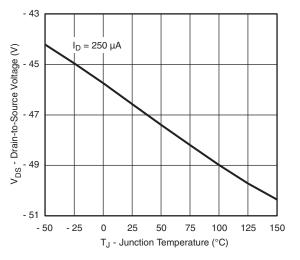
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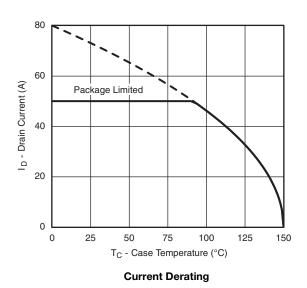
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Is - Source Current (A)





Drain Source Breakdown vs. Junction Temperature

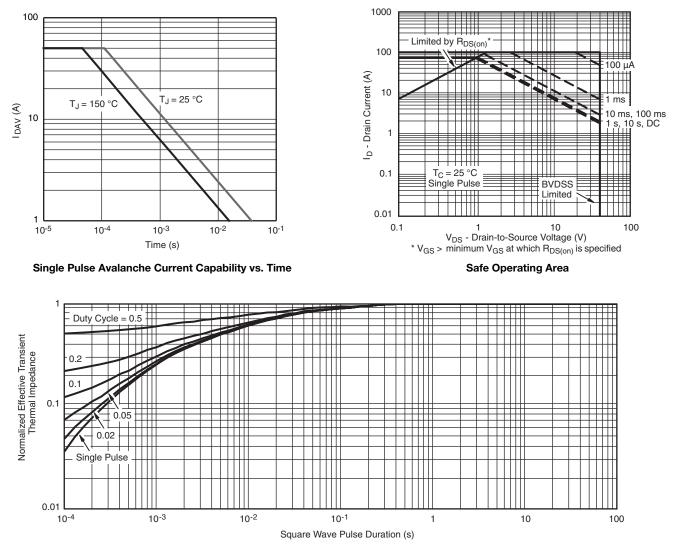


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65594.

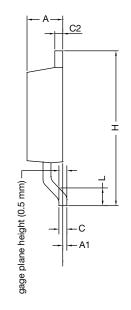


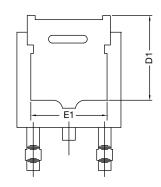
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TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
E	6.35	6.73	
E1	4.32	-	
Н	9.40	10.41	
е	2.28 BSC		
e1	4.56 BSC		
L	1.40	1.78	
L3	0.89	1.27	
L4	-	1.02	
L5	1.01	1.52	

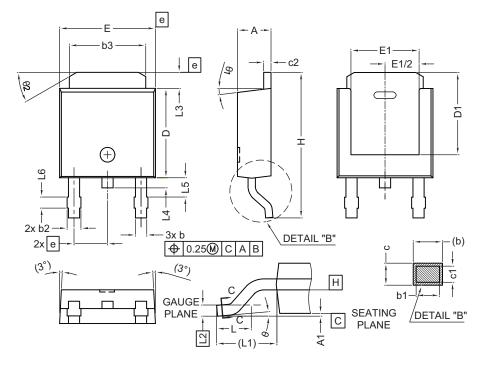
Note

• Dimension L3 is for reference only



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VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
с	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	-	
E	6.35	6.73	
E1	4.32	-	
e	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74 ref.		
L2	0.51 BSC		
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

Notes

• Dimensioning and tolerance confirm to ASME Y14.5M-1994

• All dimensions are in millimeters. Angles are in degrees

• Heat sink side flash is max. 0.8 mm

Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022 DWG: 5347

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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